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BiTS

Burn-in & Test Strategies Workshop

TM

March 6 - 9, 2016

**Hilton Phoenix / Mesa Hotel
Mesa, Arizona**

Archive- Session 5

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Session 5

Ashok Kabadi
Session Chair

BiTS Workshop 2016 Schedule

Performance Day

Tuesday March 8 - 10:30 am

West Meets East & Cutting Edge

"LPDDR4 Signal & Power Performance Optimization By Hardware"

"通过测试硬件的优化来提升LPDDR4信号和电源的性能"

Yuanjun Shi - Twinsolution Technology

Xiao Yao - HiSilicon Technologies Co

"Reliability Characterization of Unpackaged (bare) die for Silicon Photonics module"

Sujata Paul, Andrew Fong, Samir Alqadhy, Huy Nguyen, Zoe Conroy - Cisco

Tom Elliot, Jag Jassal - Evans Analytical Group

"Advanced High Energy CO2 Spray Cleaning Technology for Burn-In Test Substrate Cleaning Applications"

Nelson Sorbo - Cool Clean Technologies

"Texas Instruments Final Test Contactor Qualification Process and Low Profile Contactor Solution"

James Tong, Hisashi Ata - Texas Instruments

LPDDR4 Signal & Power Performance Optimization By Hardware

Yuanjun Shi / Twinsolution R&D
Xiao Yao / Hisilicon Test Solution R&D



2015 BiTS Workshop
Shanghai
October 21, 2015



BiTS Shanghai 2015

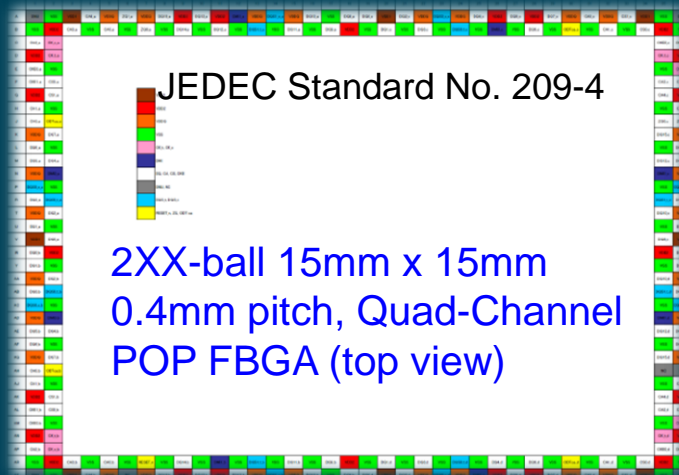
East Meets West

Contents

- DDR4 JEDEC Standard
- LPDDR4 PCB Channel & Socket SI Simulation
- LPDDR4 PCB and Socket Power Integrity Simulation
- Summary

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DDR4 JEDEC Standard



Partial Enlarge Map of DDR

	1	2	3	4	5	6	7	8	9	10
A	DNJ	VSS	VDD1	CA4 _a	VDDQ	ZQ1 _a	VDDQ	DQ15 _a	VDD2	DQ13 _a
B	VSS	VDD2	CA3 _a	VSS	CA5 _a	VSS	ZQ0 _a	VSS	DQ14 _a	VSS

This case only study one group signal pin across all four group signal pins, and only include DQ pin.

Symbol	Type	Description
CK_t_A, CK_c_A, CK_t_B, CK_c_B	Input	Clock
CA[5:0]_A CA[5:0]_B	Input	Command/Address Inputs
DQ[15:0]_A, DQ[15:0]_B	I/O	Data Input/Output: Bi-direction data bus.
DQS[1:0]_t_A, DQS[1:0]_c_A, DQS[1:0]_t_B, DQS[1:0]_c_B	I/O	Data Strobe
VDDQ, VDD1, VDD2	Supply	Power Supplies
VSS, VSSQ	GND	GND

DDR4 JEDEC Standard

Clock Jitter Specification

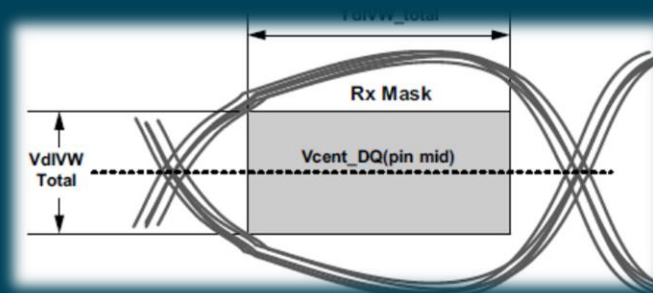
Table 88 — Clock AC Timings

Parameter	Symbol	LPDDR4-1600		LPDDR4-2400		LPDDR4-3200		LPDDR4-4266		Units	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
Clock Timing											
Clock period jitter	tJIT(per)	-70	70	-50	50	-40	40	-	TBD	ps	

Eye Diagram Specification

Parameter	Symbol	1600/1867 ^A		2133/2400		3200		4266		Unit	NOTE
		min	max	min	max	min	max	min	max		
VdIVW_total	Rx Mask voltage - p-p total	-	140	-	140	-	140	-	120	mV	1,2,3,5
TdIVW_total	Rx timing window total (At VdIVW voltage levels)	-	0.22	-	0.22	-	0.25	-	0.25	UI*	1,2,4,5

Eye diagrams are a very successful way of quickly and intuitively assessing the quality of a digital signal, for example Overlaying of bit and noise level. So Eye diagrams is a very important tools to analysis signal integrity of high speed interconnectors. On other hand we also can utilize the Eye diagram to minimize the delaying of bit as well as the transmission performance of system.



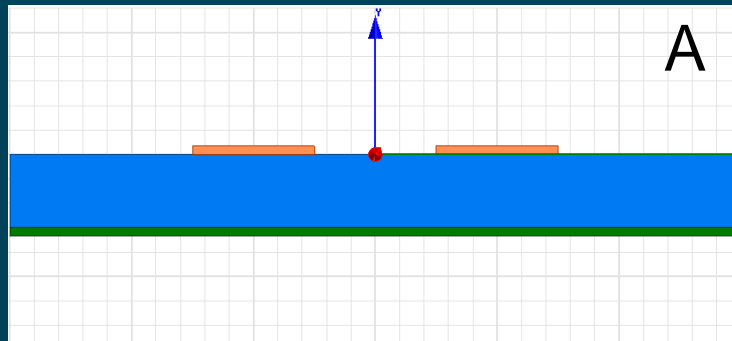
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LPDDR4 PCB Channel & Socket SI Simulation

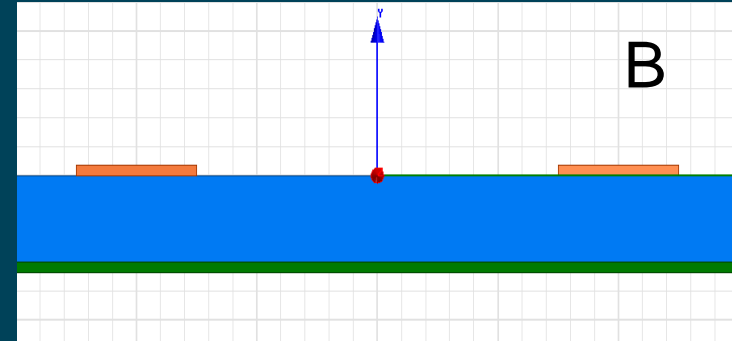
- PCB routing optimization
- Single Bit Performance
- S-Parameter Comparison Across Different Socket Structure
- Eyediagnm analysis across different socket structure

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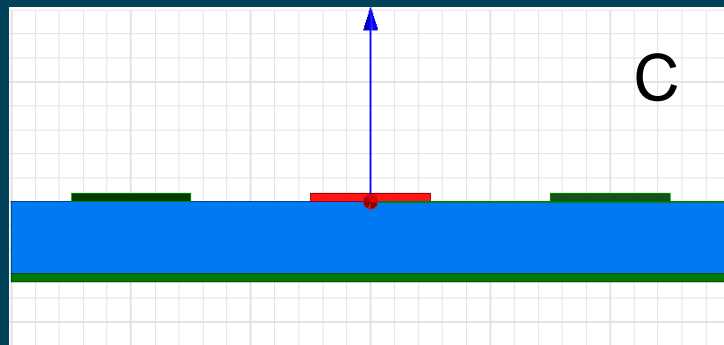
PCB Routing Optimization



1W (1 Time/1倍线宽)



3W (3 Times/3倍线宽)

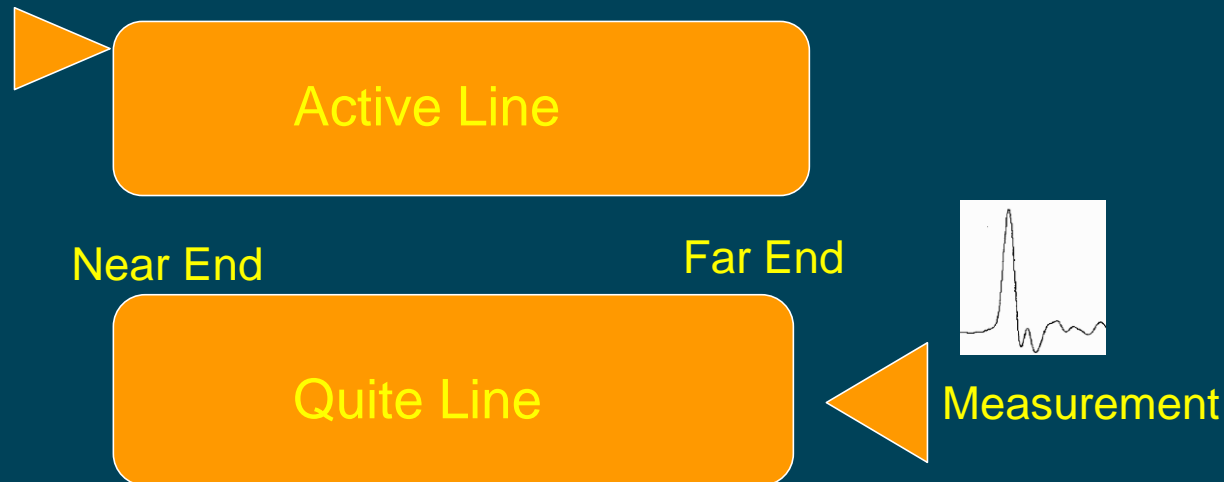


CPW (Coplanar waveguide/共面波导)

Cross Talk Simulation Circuitry

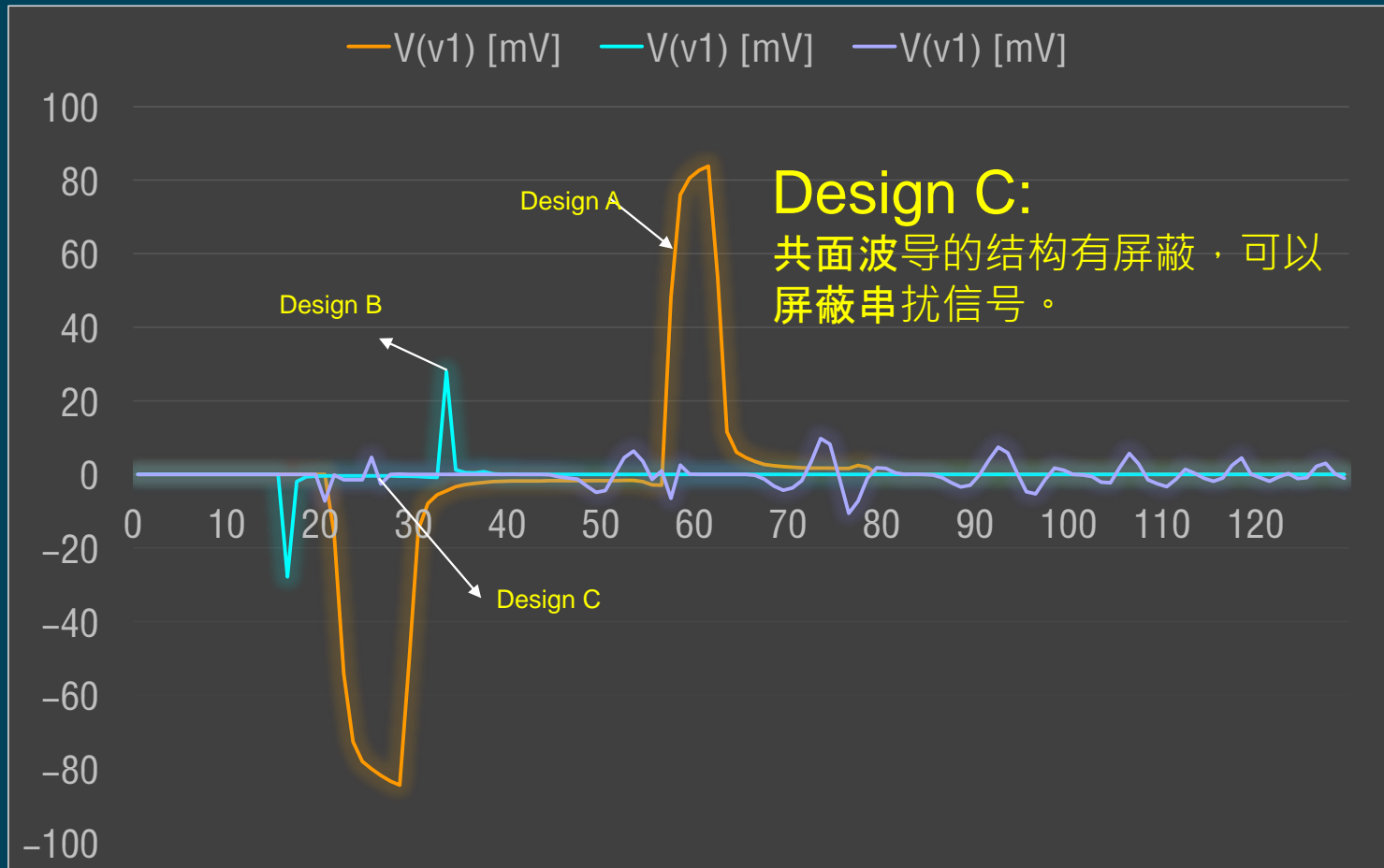


Pulse Drive Signal



Drive a pulse from active line, and using the voltage measurement probe to check the far end cross talk, and compare with different design.


PCB Cross Talk



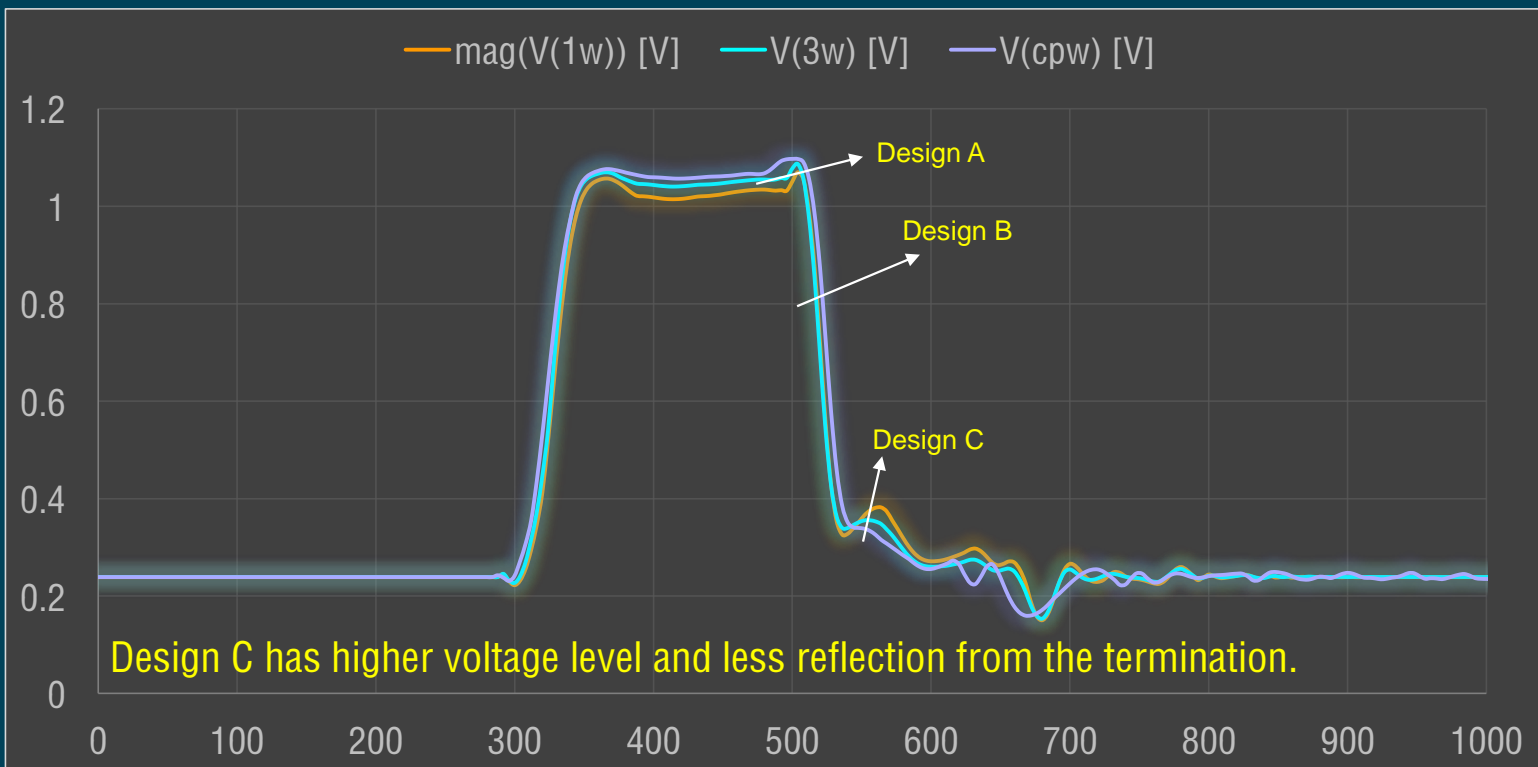
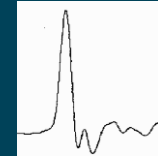
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Single Bit Simulation Circuitry

Pulse Drive



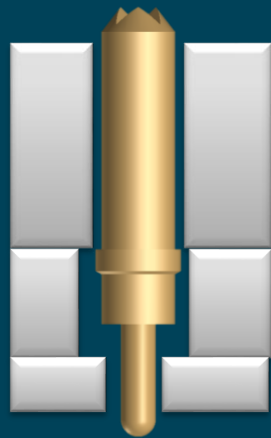

Measurement



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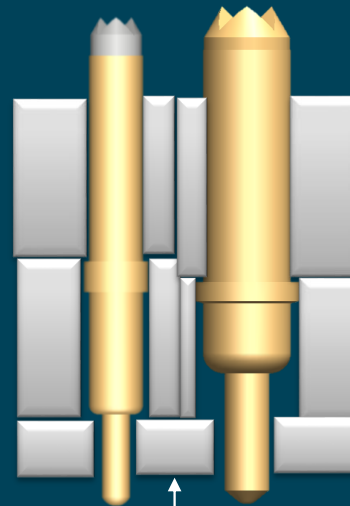
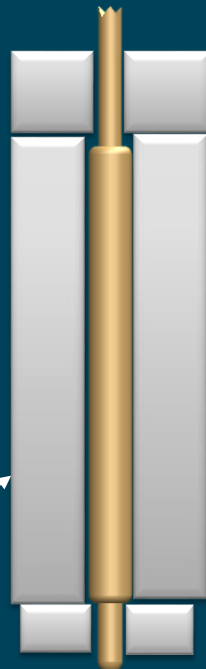
Socket Structure

Short Pin Long Pin



Insulation Material

Hybrid Socket

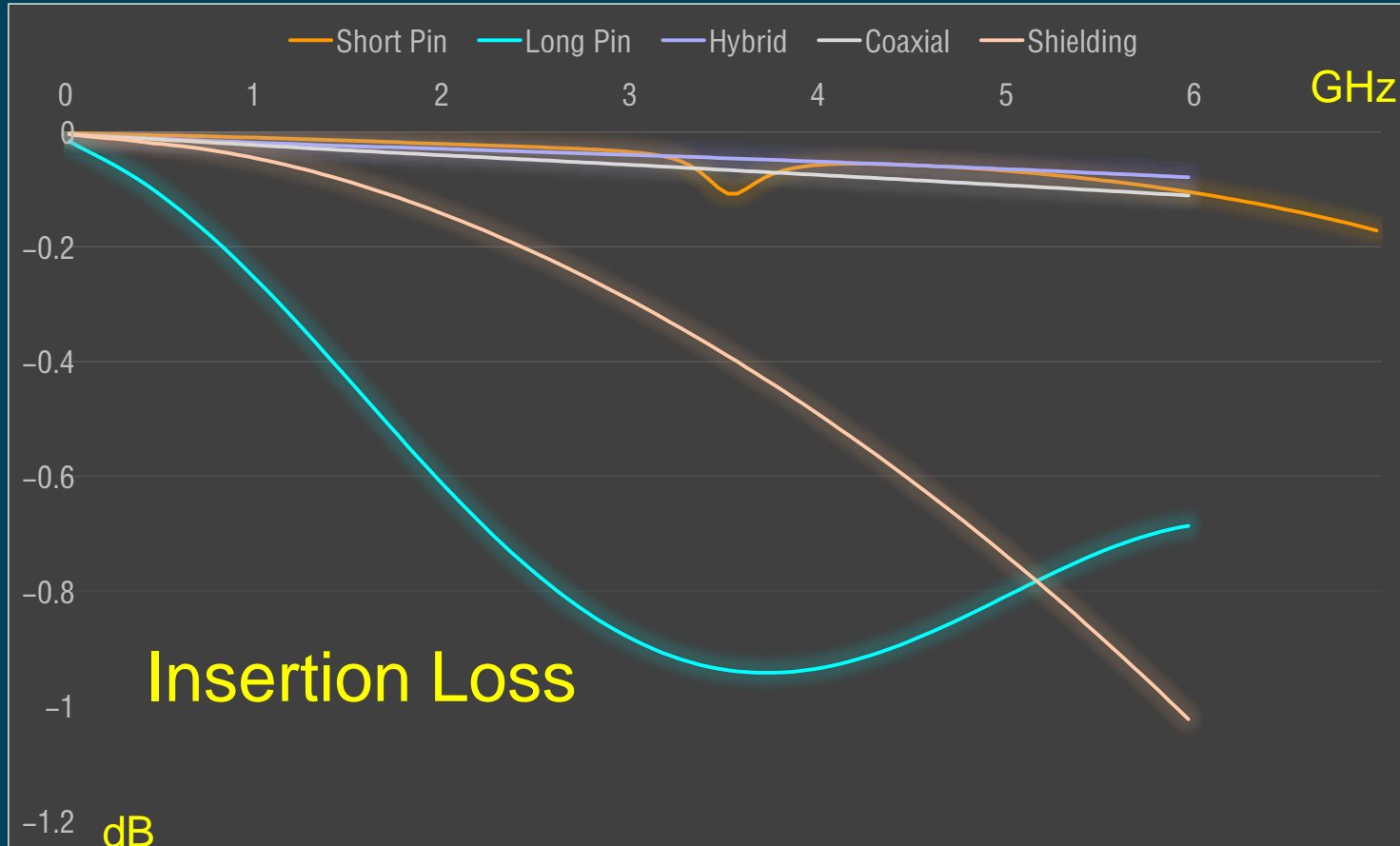


Insulation Material

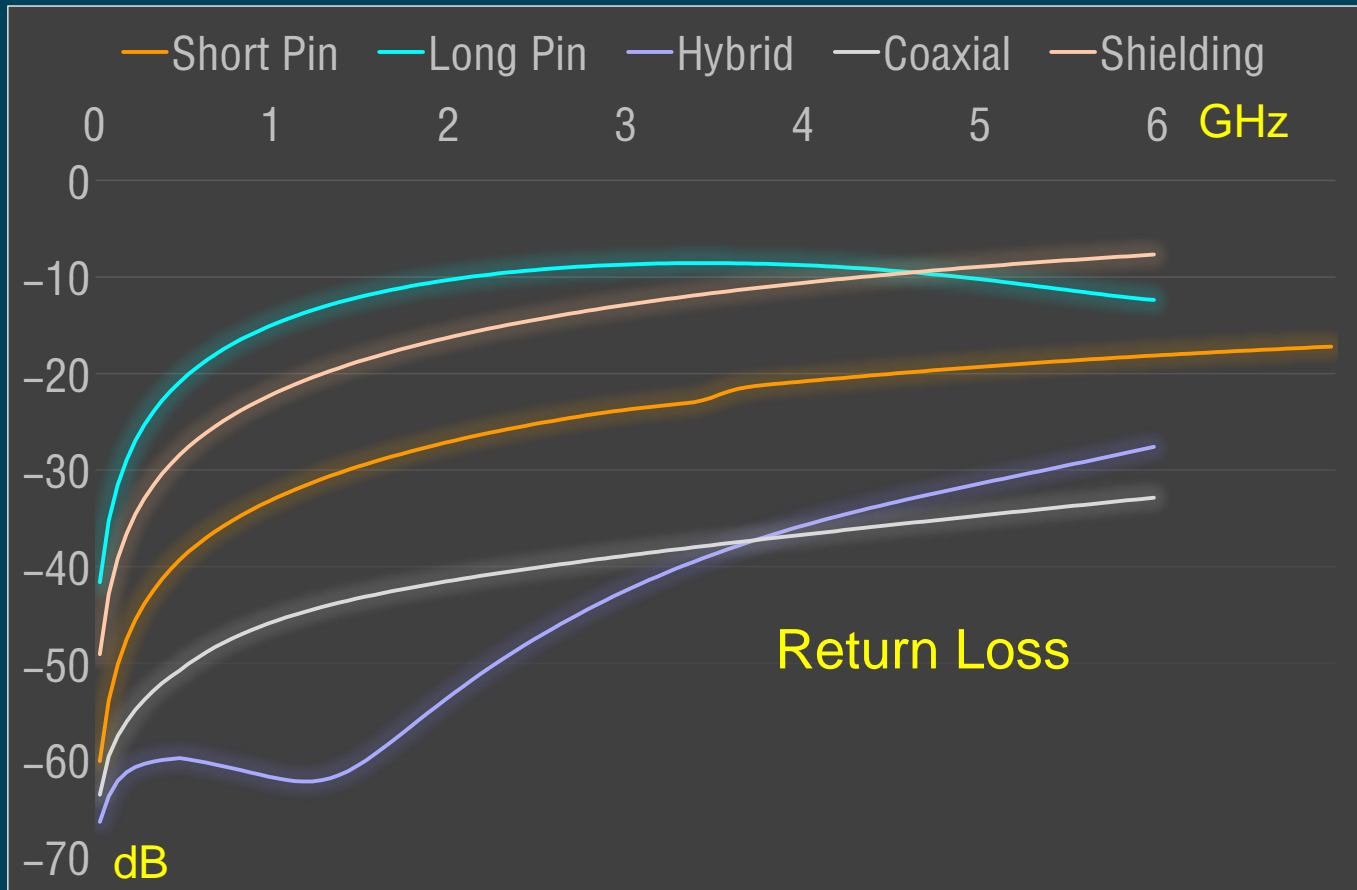
Coaxial Shielding



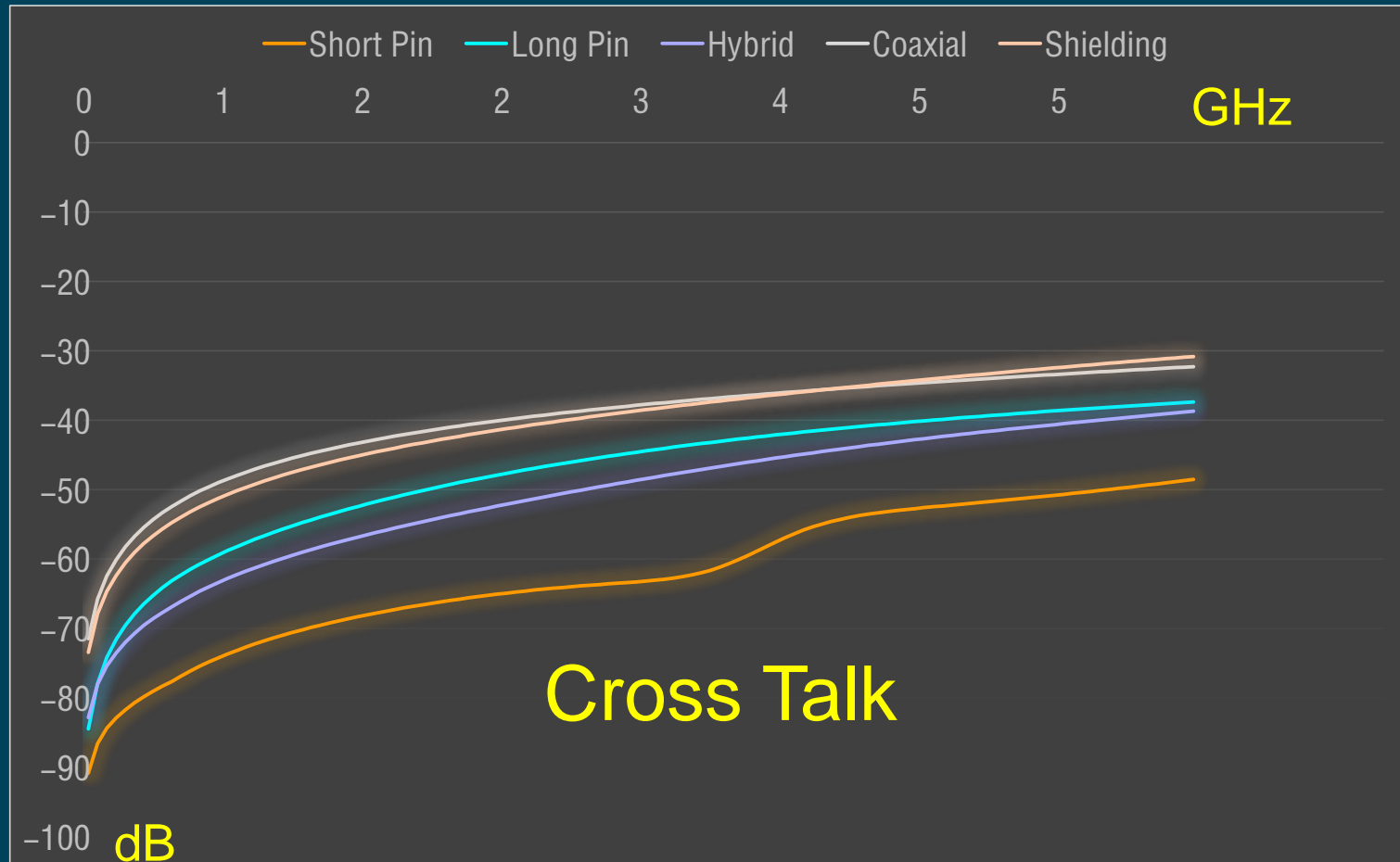
Socket S-Parameters



Socket S-Parameters

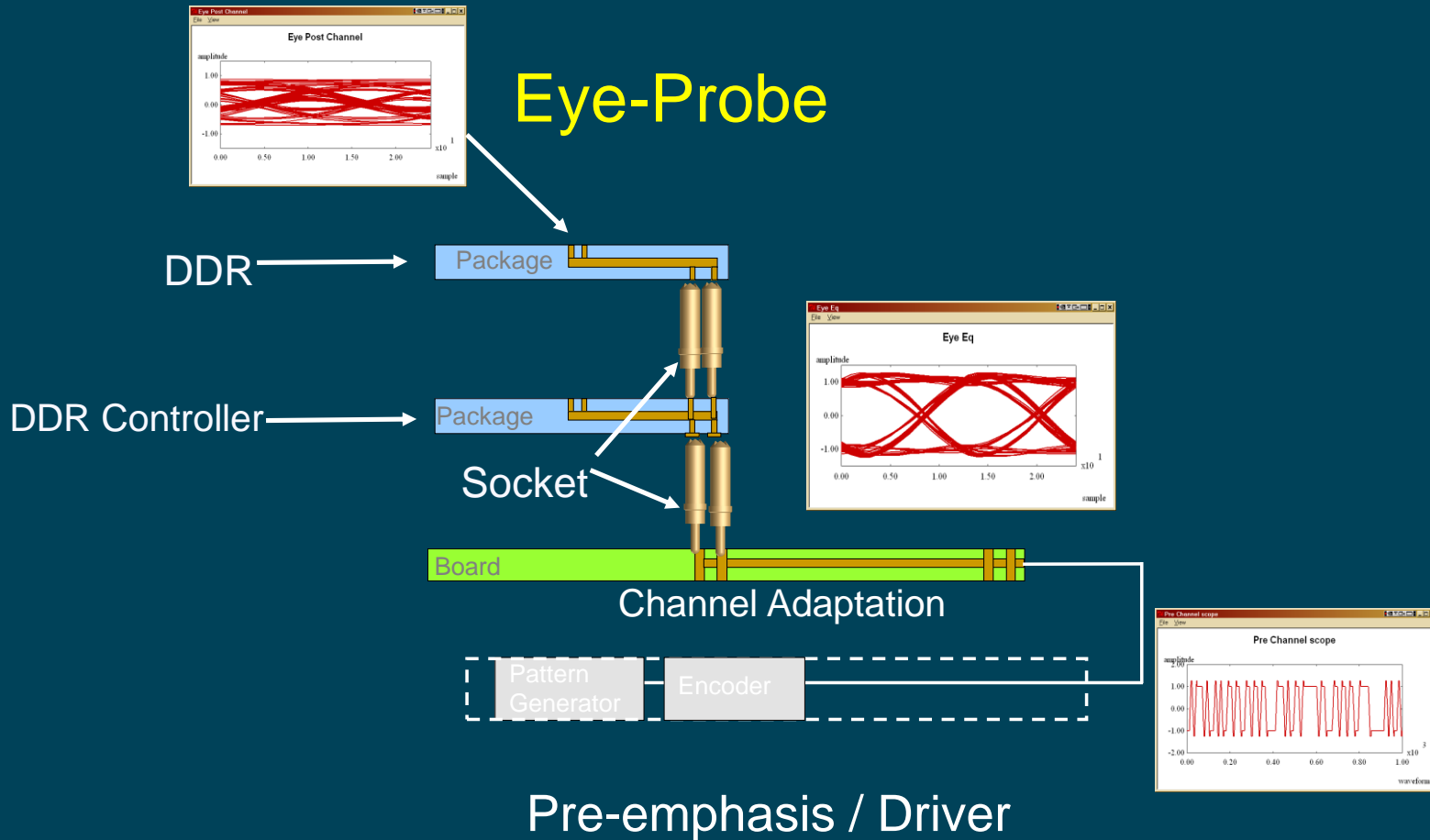


Socket S-Parameters



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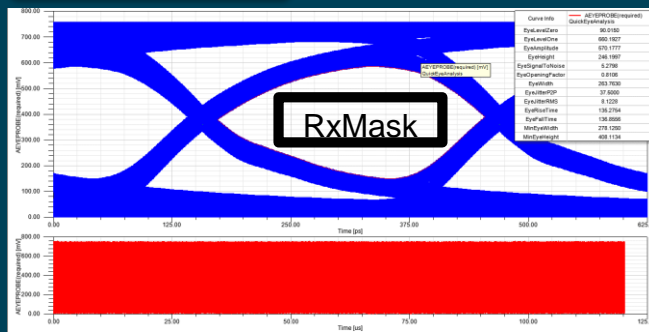
Eye Diagram Loop



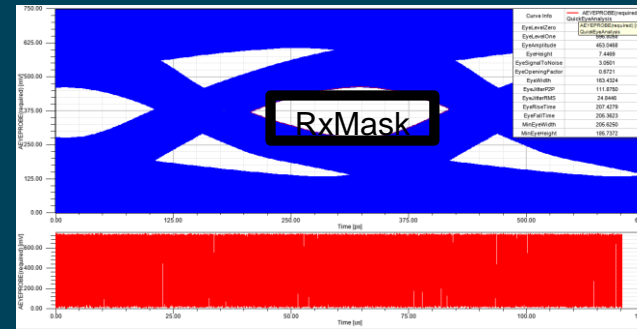
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Eye diagram Compare

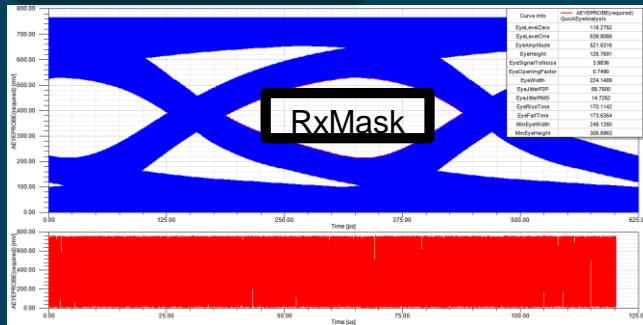
Short Pin



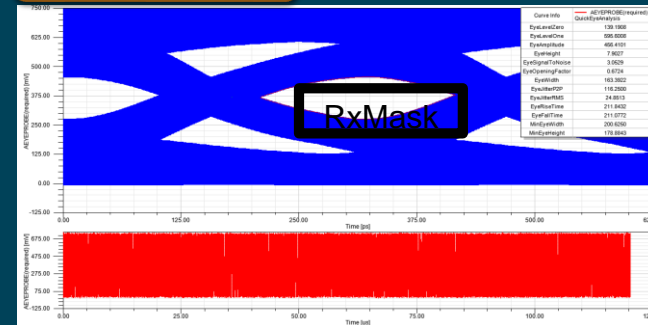
Long Pin



Hybrid Pin



Shield



Eye diagram Summary

<u>Structure</u>	<u>Jitter</u>	<u>VdiVW mV</u>
Short Pin	0.038	247
Long Pin	0.112	7.5
Hybrid	0.069	129
Coaxial	0.031	298
Shielding	0.117	7.9

Jitter Spec: 0.04

TdivW: 79ps

VdiVW: 140mV

High volume manufacturing sensitivity analysis

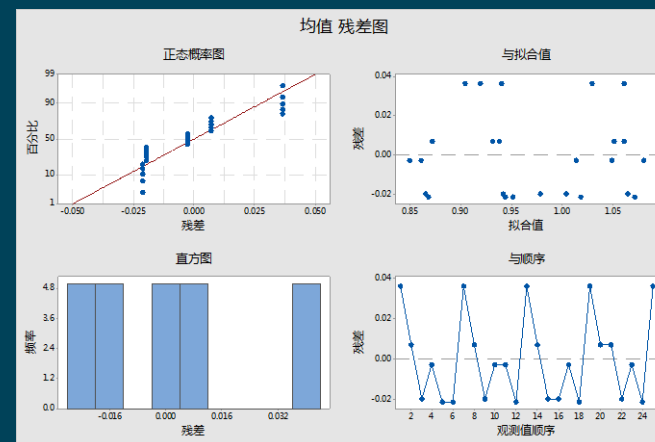
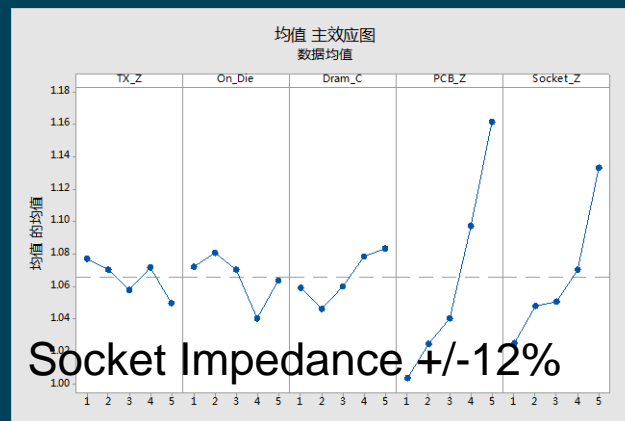
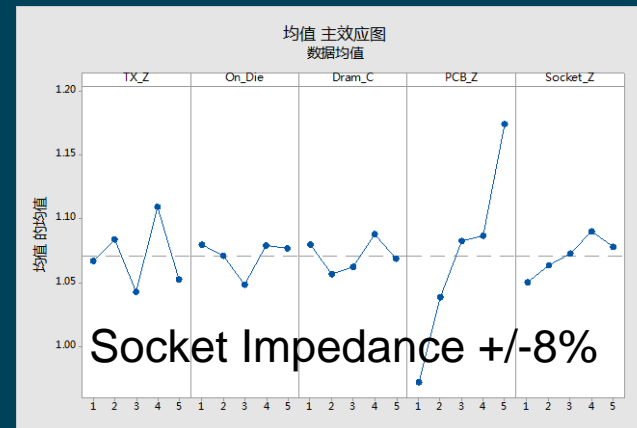
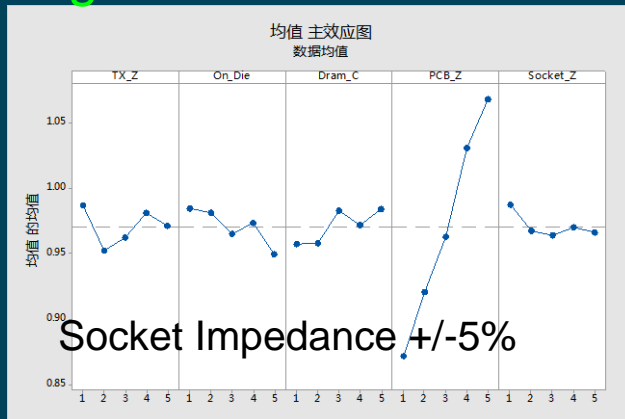
Channel Parameters

Variation

Tx driver impedance (ohm)	34 +/- 10%
On-die-termination (ohm)	60 +/- 20%
DRAM Ci (pF)	2 +/- 10%
PCB trace impedance (ohm)	55 +/- 15%
Socket Impedance(ohm)	50+/-5%

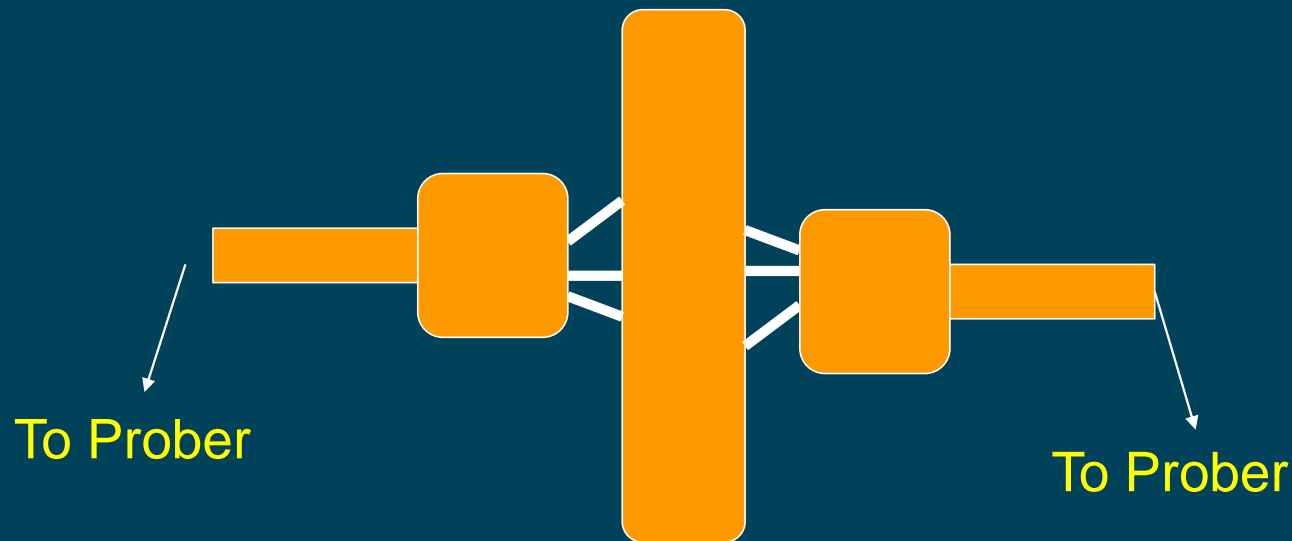
High volume manufacturing sensitivity analysis

Taguchi DOE/田中实验



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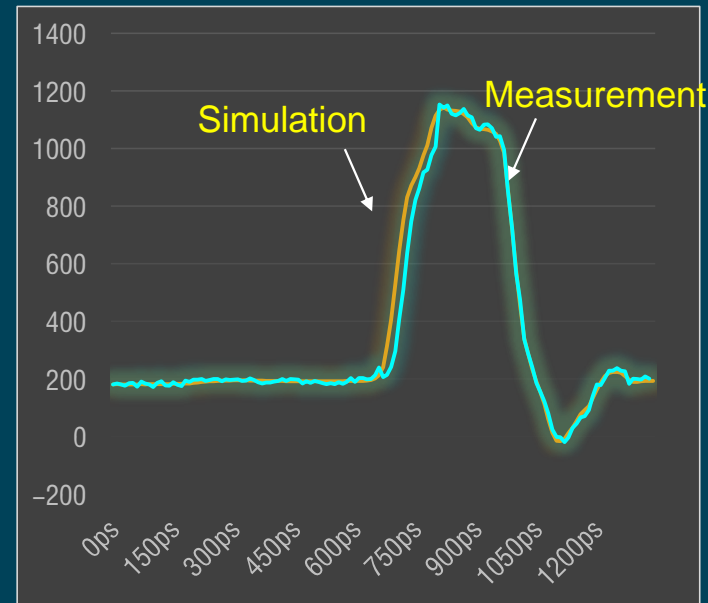
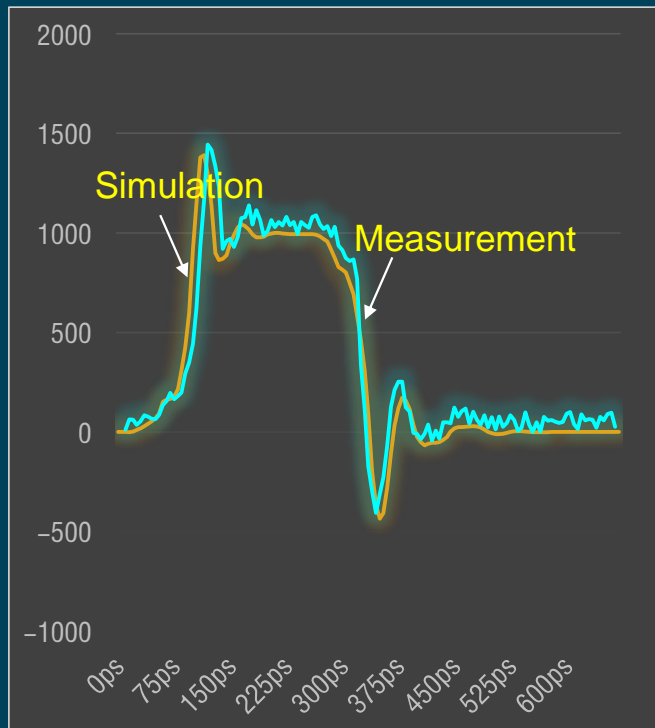
Simulation Vs Measurement Correlation



Socket Build Base on Pin Map

Simulation Vs Measurement Correlation

Pulse Configuration A →



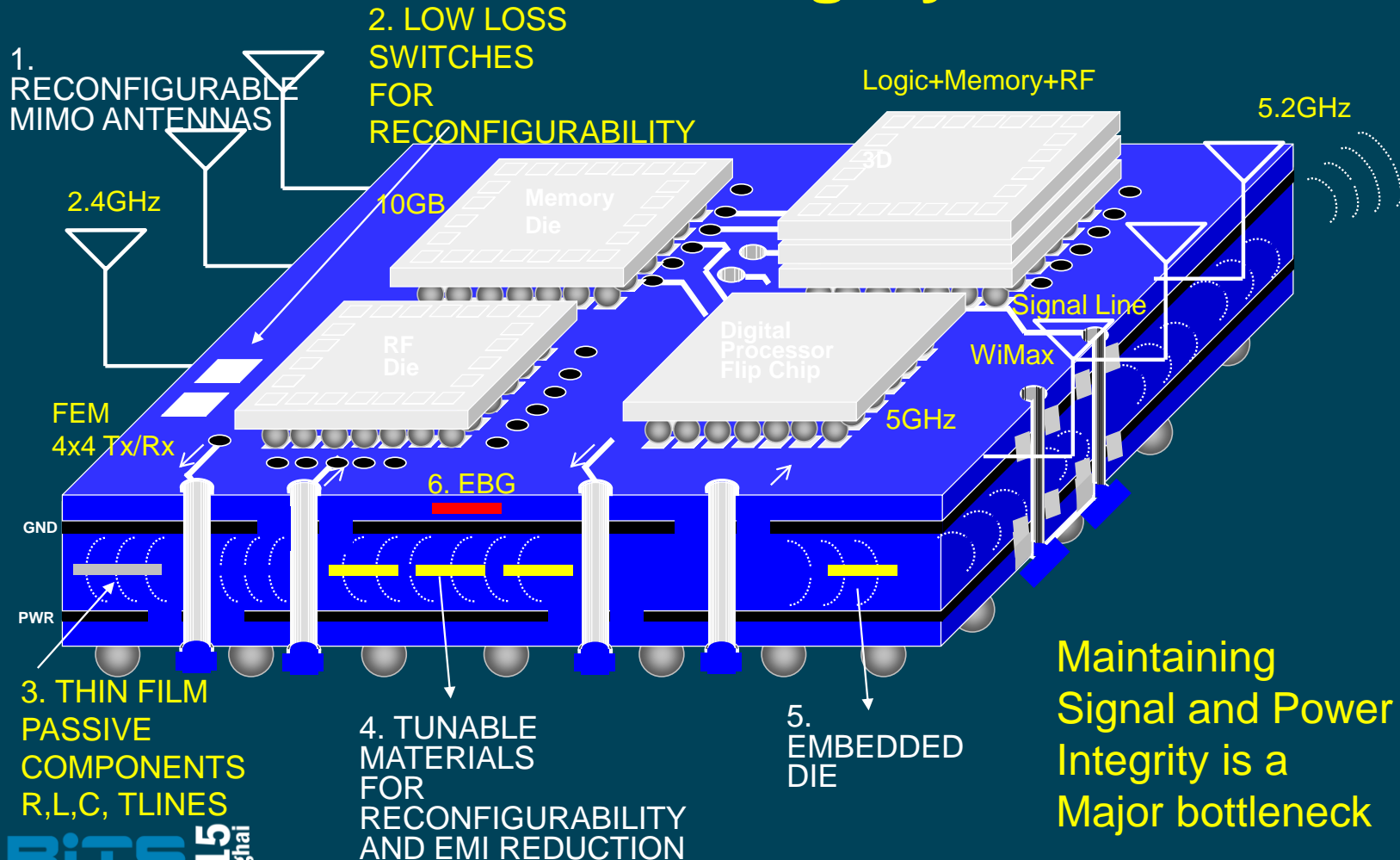
← Pulse Configuration B

LPDDR4 PI Simulations

- PI Basic
- PCB Impedance
- Socket Power Impedance Vs System Impedance
- Impedance Optimization

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Power Integrity

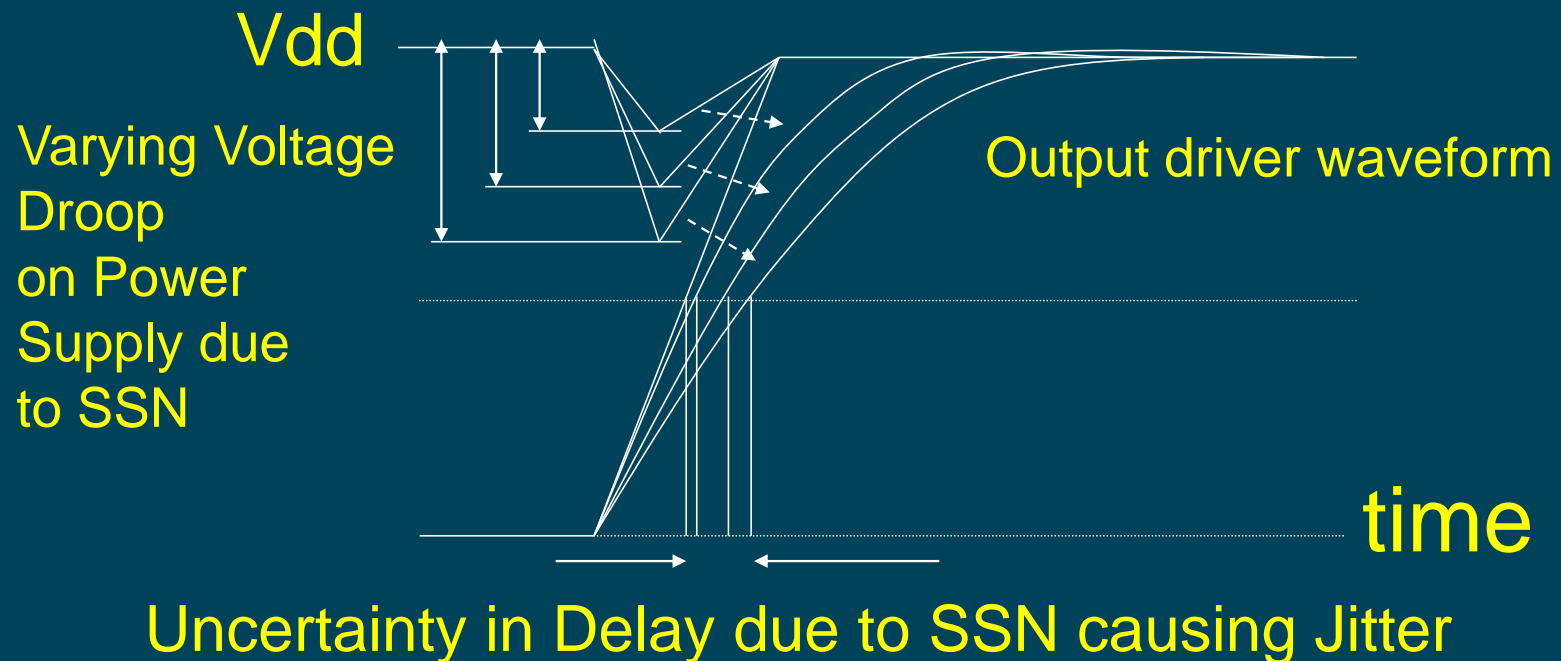


Maintaining Signal and Power Integrity is a Major bottleneck

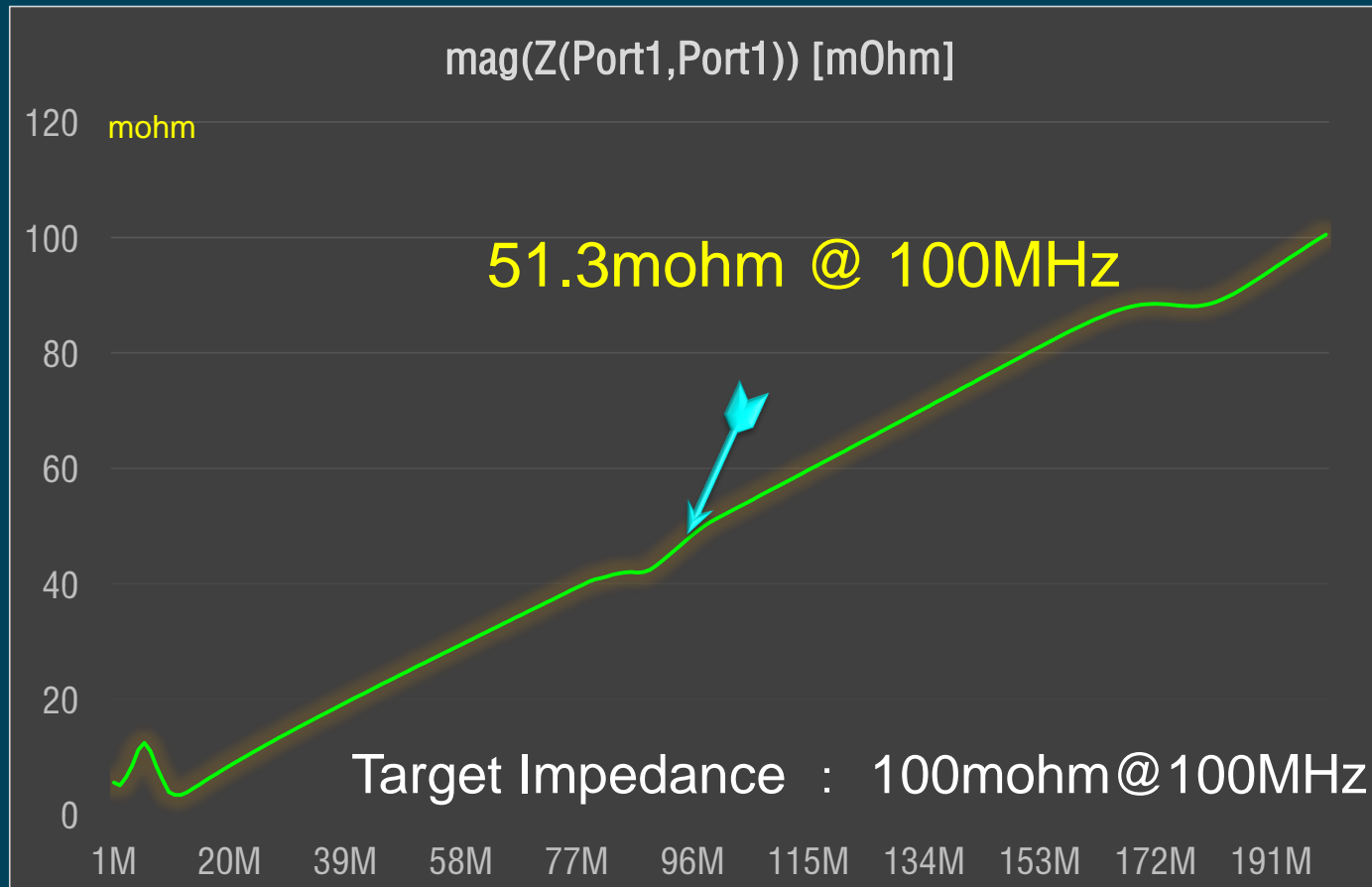


LPDDR4 Signal & Power Performance Optimization By Hardware

Jitter caused by SSN for I/O



PCB Power Impedance

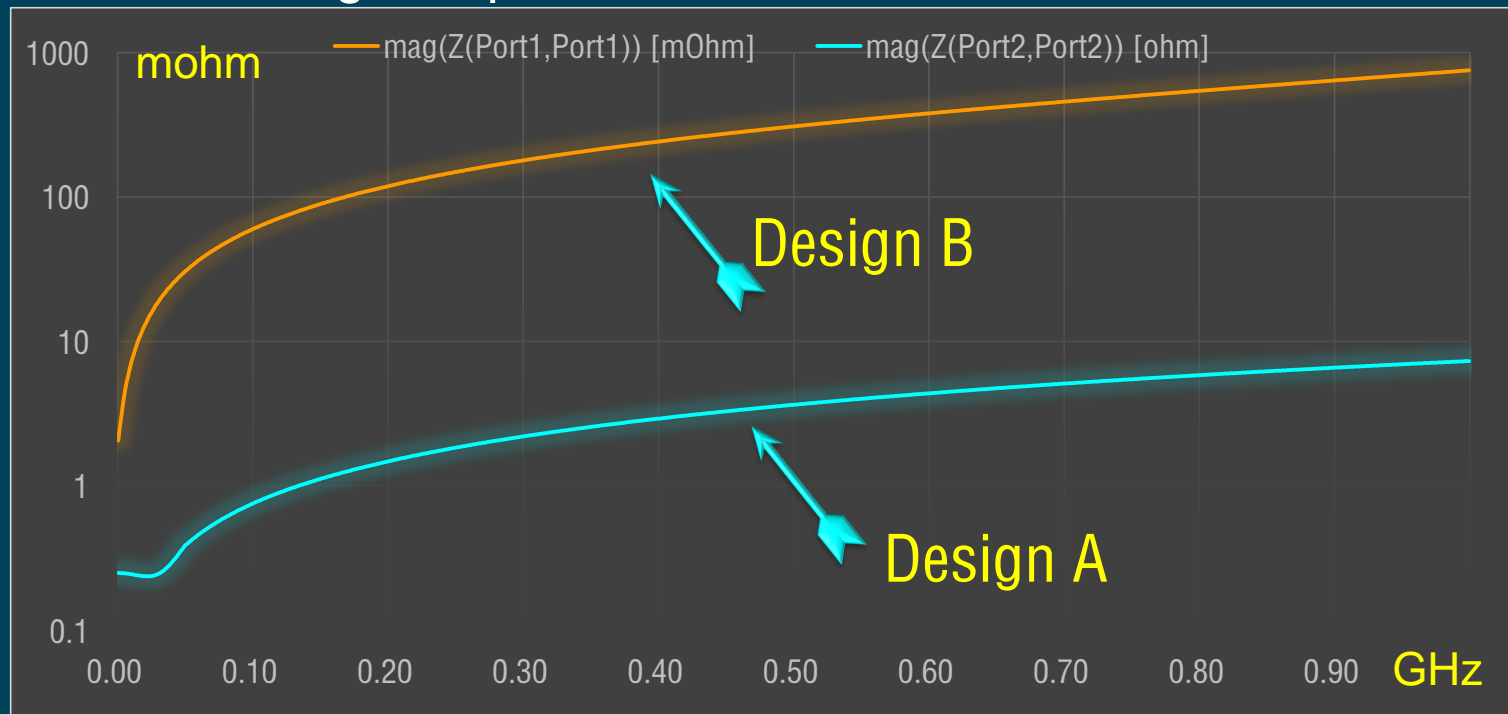


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East Meets West

Socket Power Impedance

Target Impedance : 100mohm@100MHz

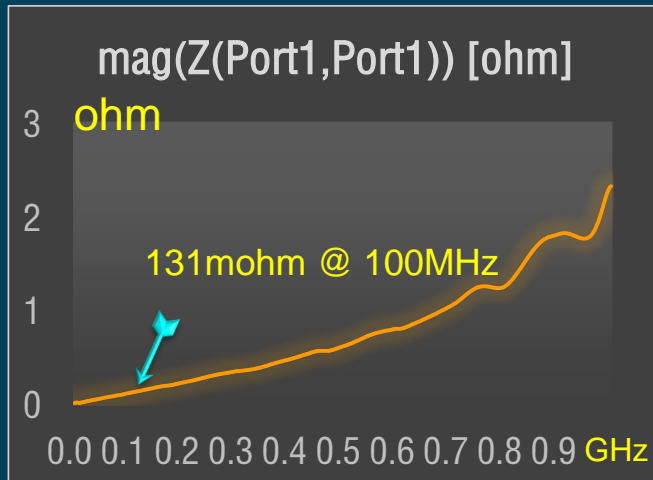


Long pin and short pin has significant difference in terms of power impedance if only measure socket only.

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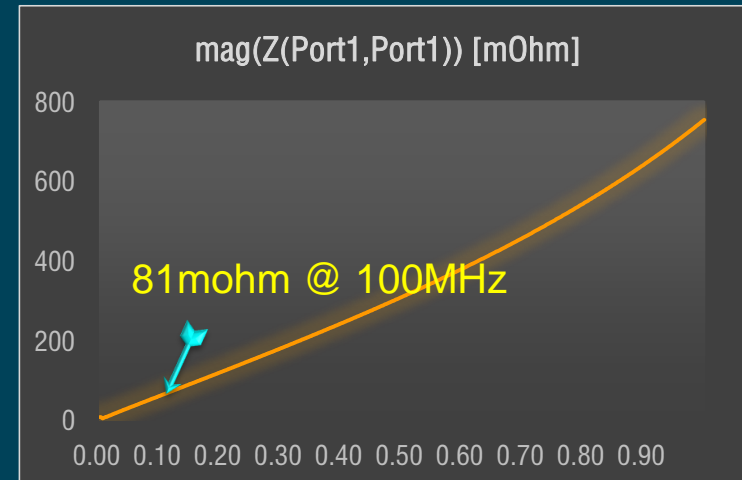
PCB + Socket + Package Impedance

Target Impedance : 100mohm@100MHz



Before

1. Increase the power plane width, and short the distribution length.
2. Optimize the pin length and diameter.
3. Although socket is not the main factor for the power impedance, however an optimized socket design and contactor selection also help the power impedance certain.

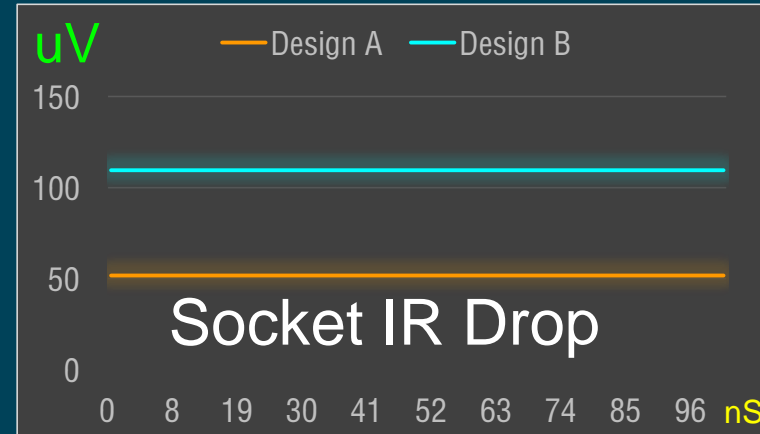
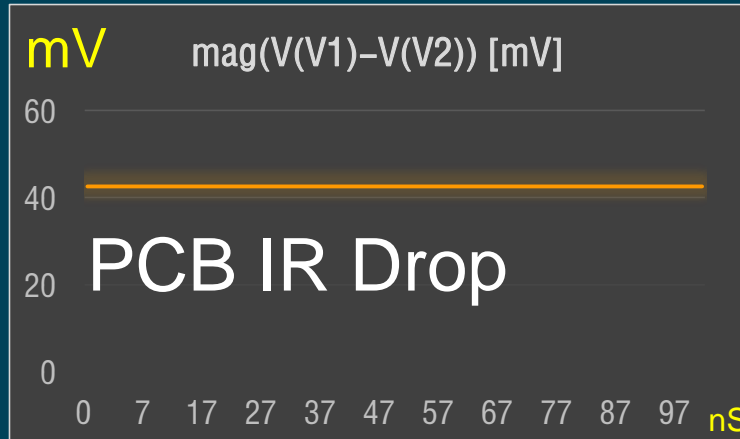


After optimized

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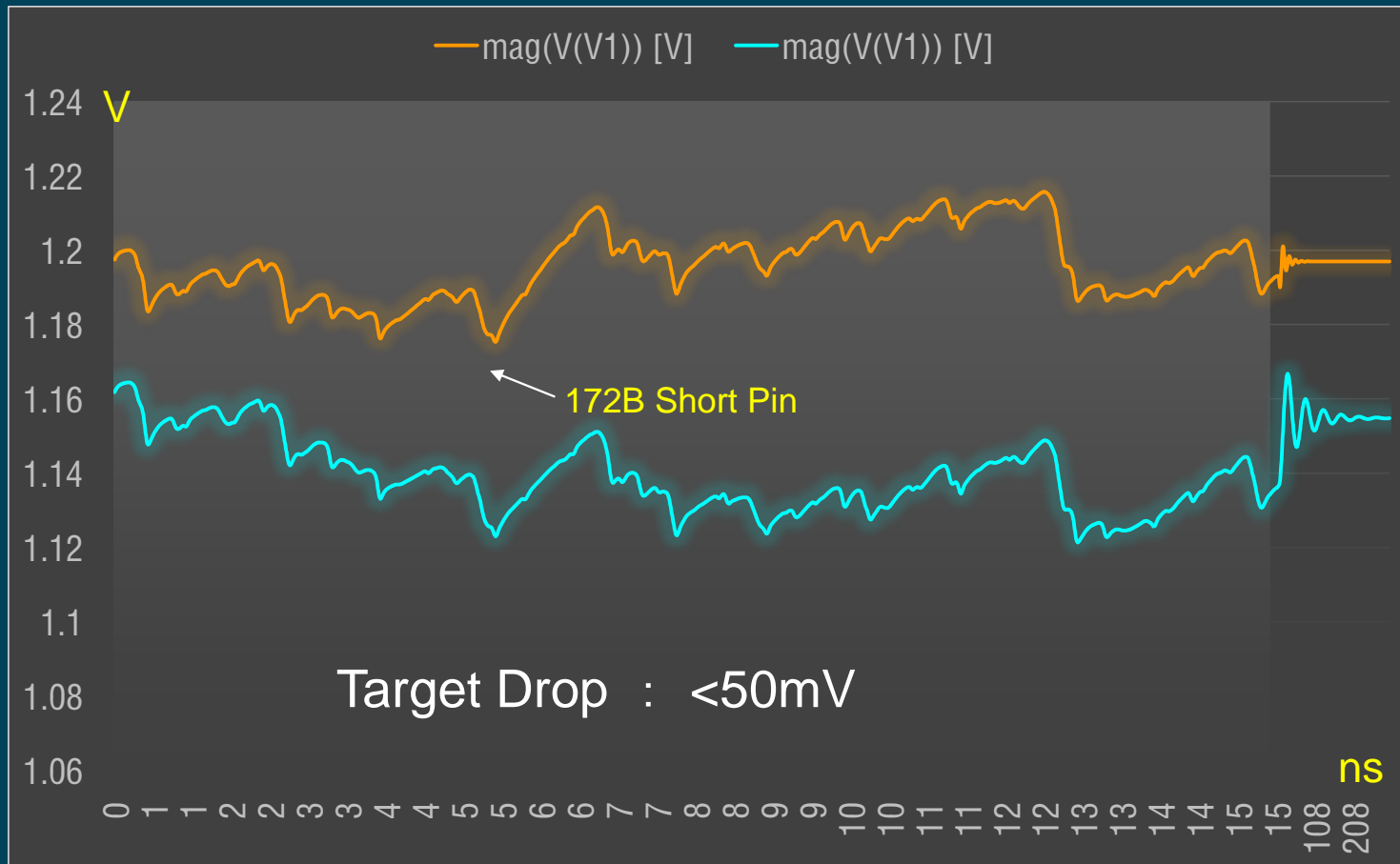
IR Drop

Target Drop : <50mV



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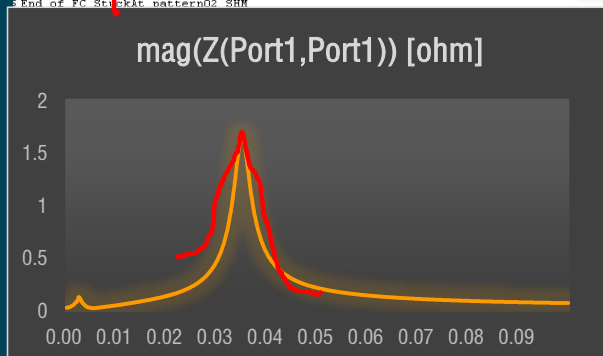
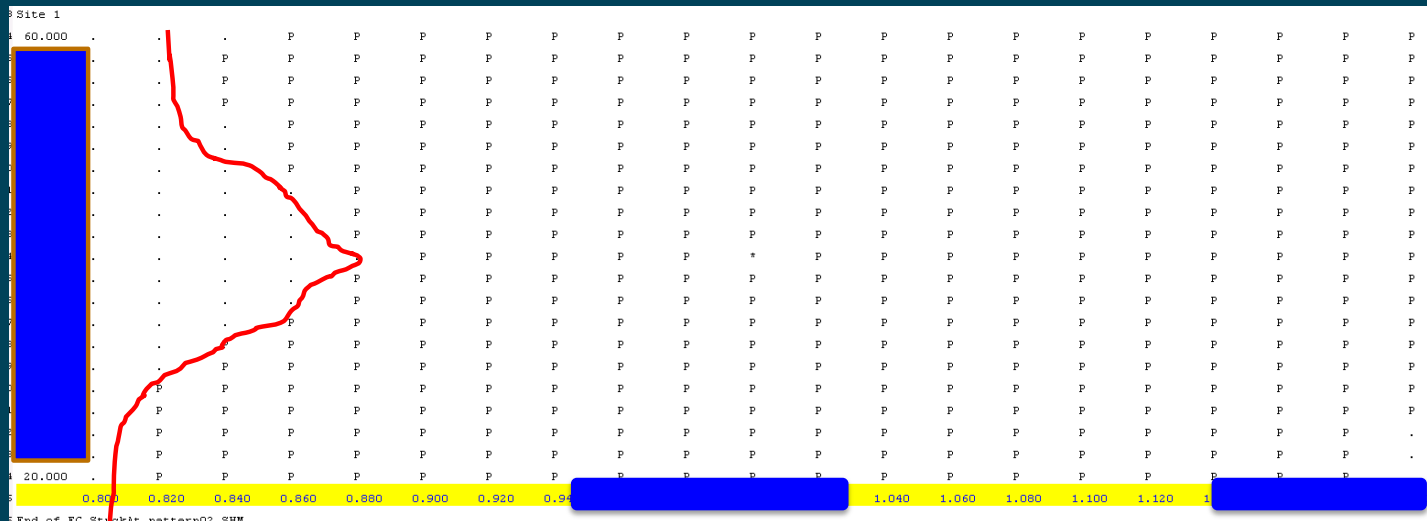
Power Transient



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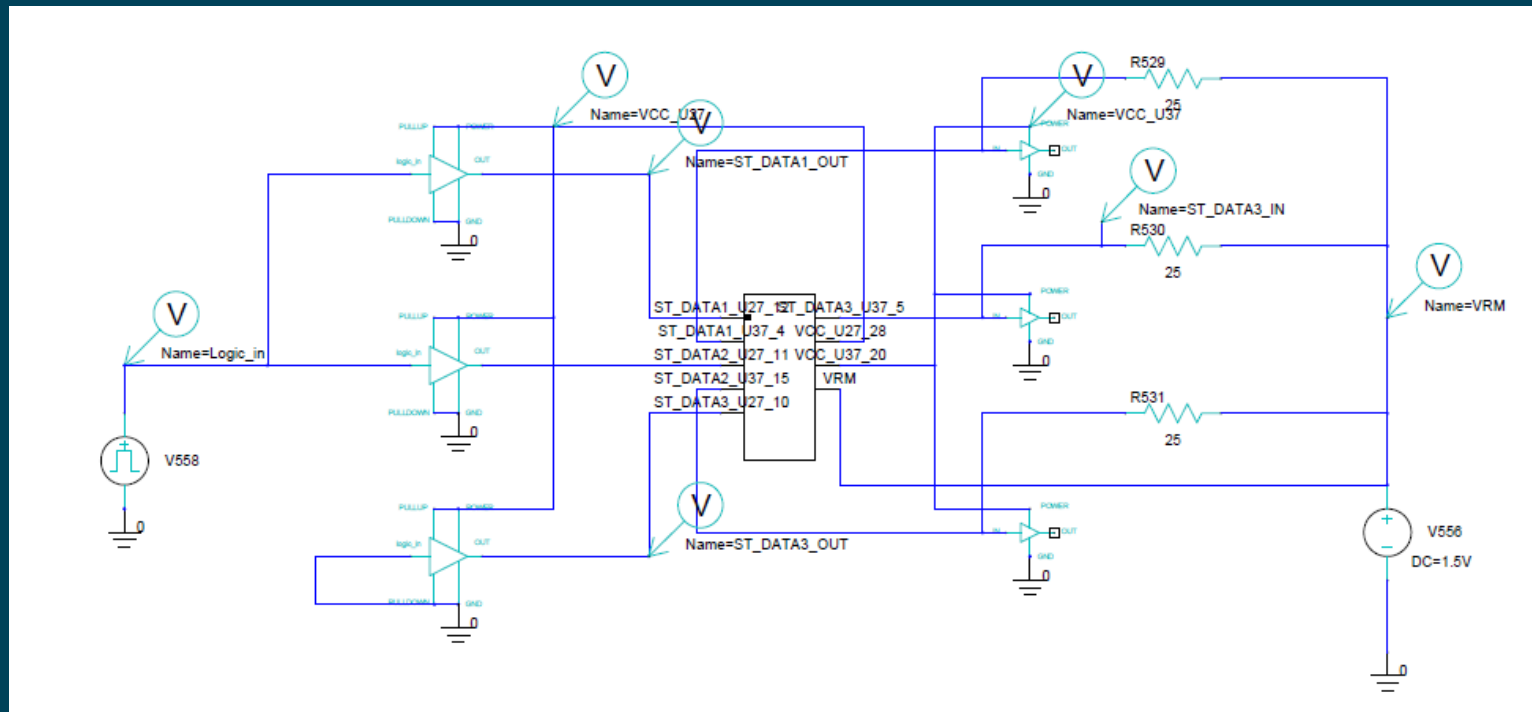
East Meets West

Power Impedance Vs Shmoo Measurement



1. SHMOO shows the controller fail curve is quite close to the power impedance simulation data.
2. The resonance frequency for simulation and measurement is also close.

Future Work



Summary

- Discussion one method to study whether the hardware can meet the LPDDR4 specification.
- Discussion one method to identify the main factor for the whole SI chain.
- Optimize the socket and pin layout to meet the power impedance performance.
- Utilize Shmoo to correlate the power impedance data.